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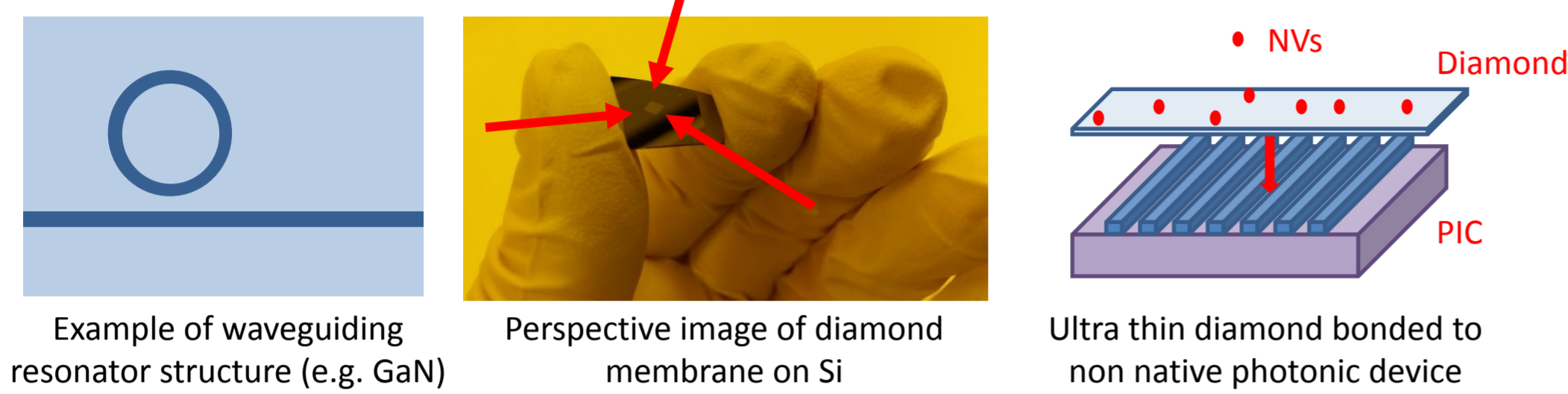
# Integrating Diamond with GaN Photonic Devices

Paul Hill, Hangyu Liu, Ross Leyman, Erdan Gu, Martin D. Dawson, Michael J. Strain.

## Motivation

Diamond has many defect centres. Some of these can be optically accessed for quantum applications like:

- Long lived solid state spin qubit memories (at RT)
- Quantum entanglement for cryptography & parallelisation



Maximising collection of zero phonon line photon emission is of interest. Guided wave devices allow enhancement of the light-matter interaction in small mode volume devices.

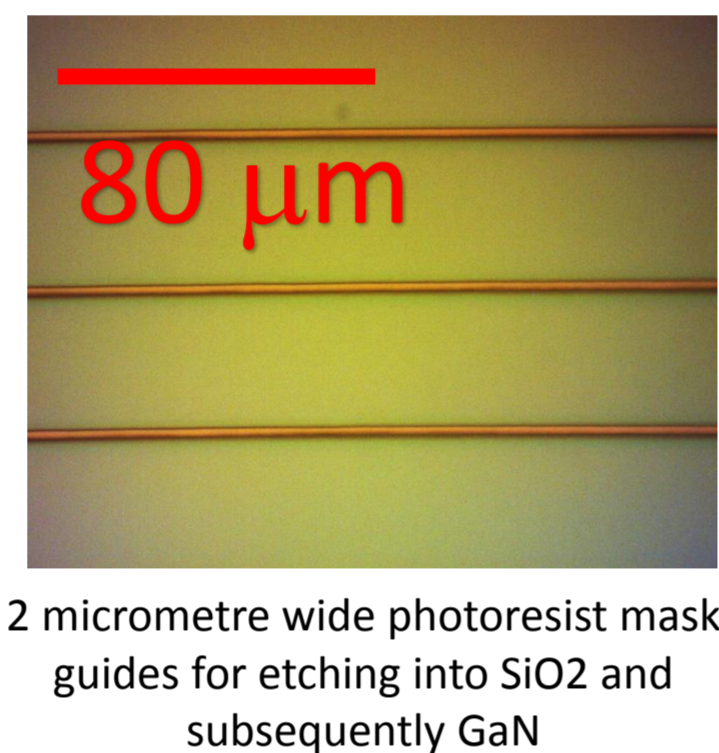
Diamond defects close to the surface of fabricated ultra-thin membranes can be coupled to these devices allowing processing of defect emissions across large area PICs.

## Fabrication of GaN devices

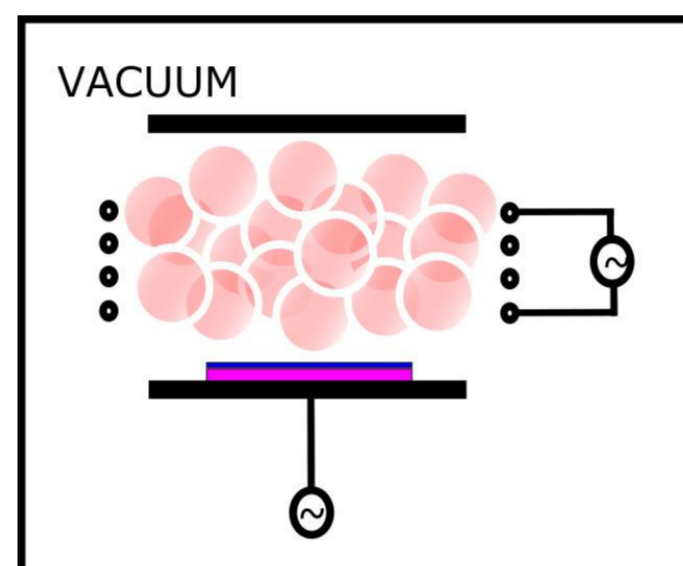
Mode simulations were conducted to find coupling percentages between GaN devices and Diamond membranes of certain thicknesses.

Devices were fabricated as follows:

- PECVD SiO<sub>2</sub> masking layer (~500nm)
- Photoresist soft mask using DLW
- RIE into SiO<sub>2</sub> hard mask
- ICP-RIE into GaN



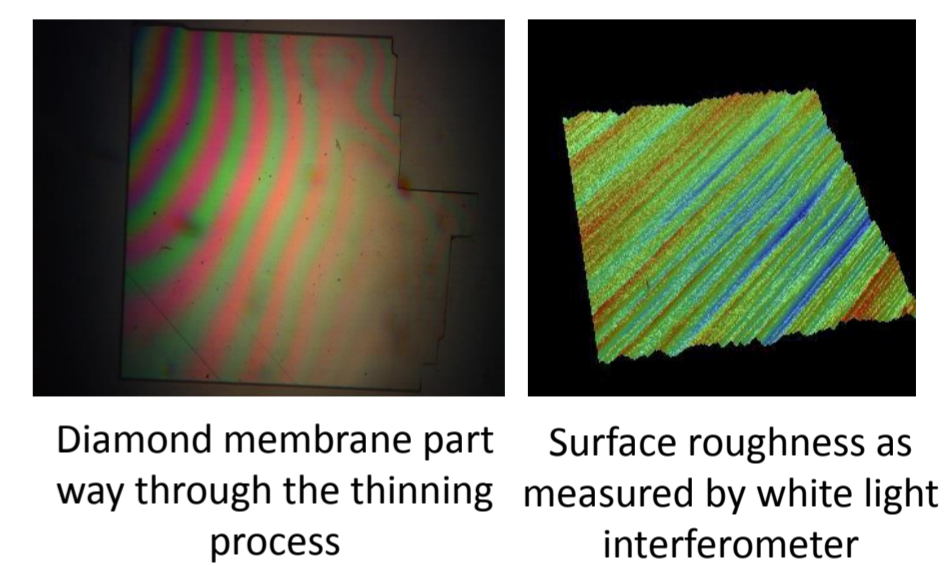
## Fabrication of Ultra-thin Diamond Membranes



Inductively coupled plasma (ICP) etching uses an RF coil to generate a plasma above a sample on a biased platen. Changing parameters such as coil or platen power, etch speed or selectivity can be controlled.

### ICP diamond etching - advantages

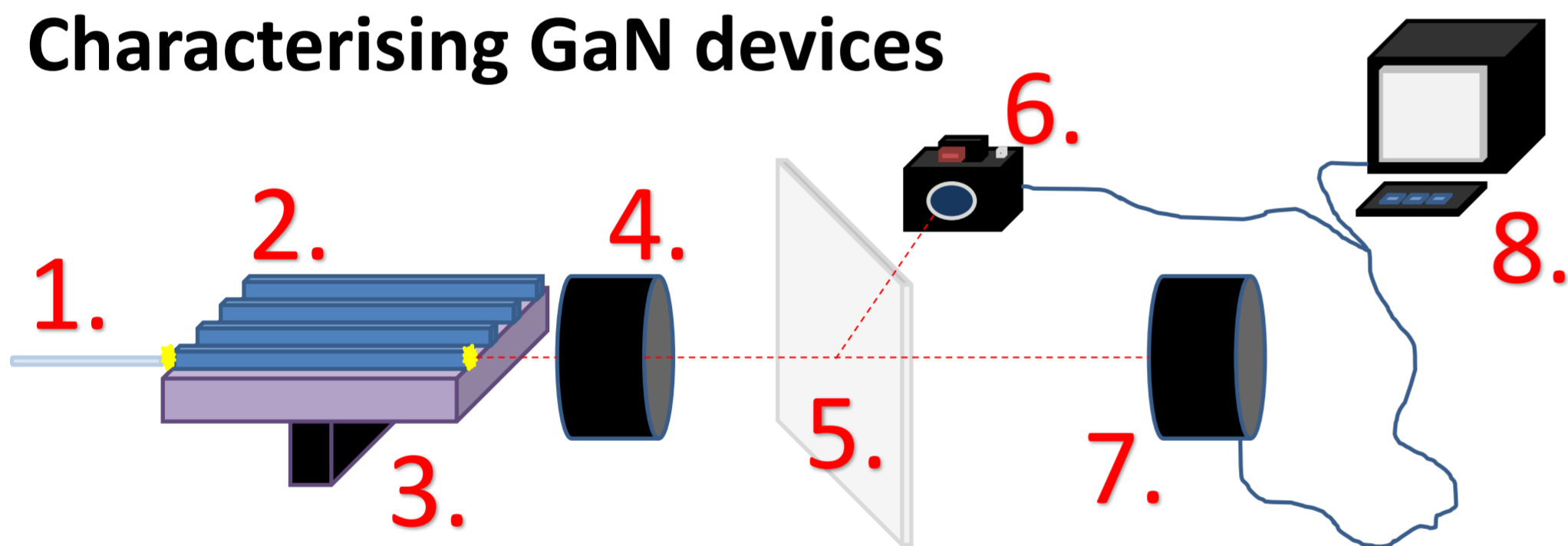
- Good control over anisotropy
- Non-graphitising
- Surface roughness improved
- High etch rate



Diamond membrane part way through the thinning process

Surface roughness as measured by white light interferometer

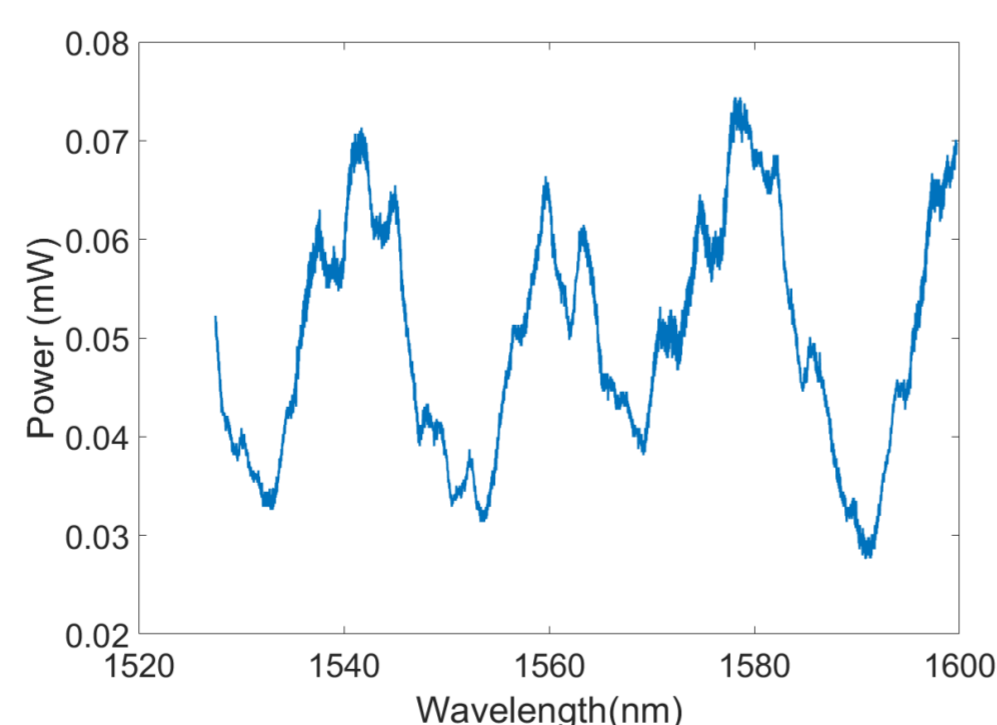
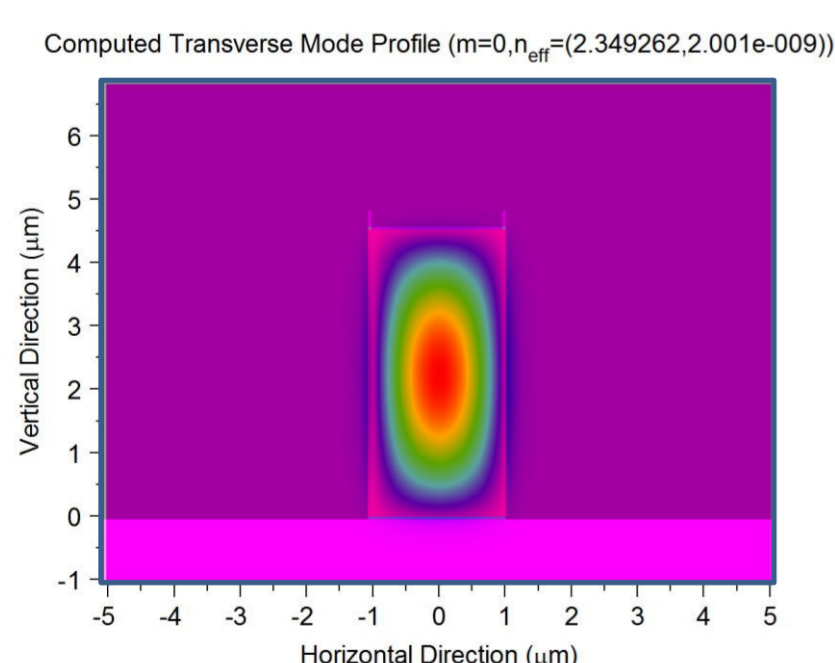
## Characterising GaN devices



A taper-ended fibre (1) coupling through the end facet of a GaN waveguide (2) on sapphire. The sample is on a movable stage (3) and is focused with an objective (4) through a beam splitter (5) onto both a camera (6) and a power detector (7) attached to a computer (8) for signal processing.

### Results of GaN waveguide device

Power readings were measured over a wavelength sweep from 1525 to 1600 nm without the sample present to measure the losses of the system.



- Total TE insertion losses = -6.3 dB

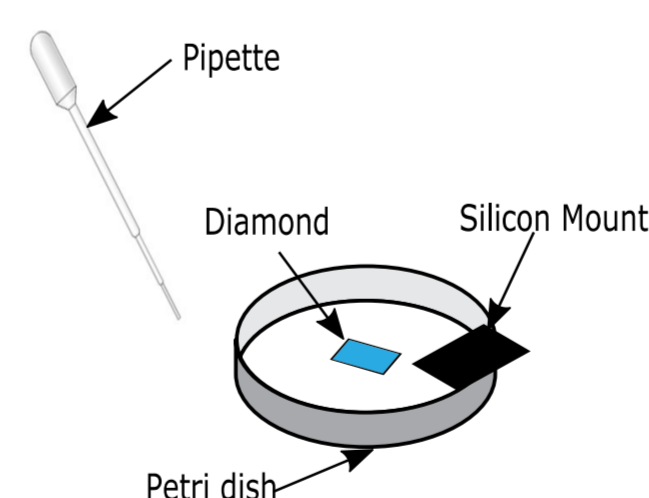
The wavelength sweep is repeated with the sample in place coupled to each waveguide. A mode calculation overlaid with the waveguide geometry is shown in the figure on the left and the power detected from light coupled through a typical waveguide is shown on the right.

ICP processing has been used to produce diamond, micro-lenses<sup>1,2</sup>, waveguides<sup>3</sup>, and raman lasers.<sup>4</sup>

Using an Ar/Cl<sub>2</sub> etch recipe, diamond etches at ~60 nm/min has been shown to reduce r.m.s. surface roughness from 0.53 nm to 0.19 nm.<sup>1</sup>

### Handling of thin film diamond

Diamond is a low toughness material and with thinning to micron and sub-micron thicknesses, processing requires care.



Tweezers must be avoided and films moved by floating the sample onto larger handle substrates using solvent immersion and agitation via pipette.

### Results

Fabrication of ultra-thin diamond membranes of **below 200 nm** have been achieved. In partnership with the NQIT project and Oxford Materials department, membranes have been bonded to a DBR mirror stack for micro-cavity enhancement of NV<sup>-</sup> emission.<sup>5</sup>

## Outlook

- Hybrid coupling of diamond optics to mature Photonic Integrated Circuit Technology
- Deterministic coupling of defect centres to on-chip devices
- Active control of resonator devices for wavelength tuning

### References

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5. Sam Johnstone, Jason Smith, Department of Materials, University of Oxford, unpublished.